

10/561865

PATENT APPLICATION

IAP20 Rec'd PCT/PTO 21 DEC 2005

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Nobuaki MITAMURA et al.

Application No.: New U.S. National Stage of  
PCT/JP2004/007252

Filed: December 21, 2005

Docket No.: 126363

For: A METHOD FOR PRODUCING A SINGLE CRYSTAL AND A SINGLE CRYSTAL

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- ☒ 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- ☒ 2. Relevance of the non-English language references 1, 4 and 5 are discussed in the present specification.
- ☒ 3. The references 1-3 were cited in an International Search Report. An English language version of the International Search Report is attached for the Examiner's information.
- ☒ 4. English language Abstracts of the non-English language references 1-3 are attached hereto.

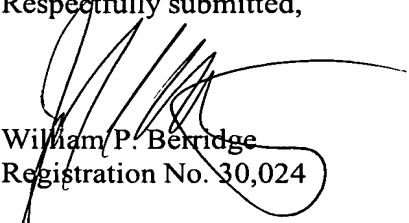
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5. A computer-generated English language translation of the following Japanese Patent Publication has been obtained from the website of the Japanese Patent Office (<http://www.jpo.go.jp>), and is attached, but has not been reviewed for accuracy. See References 1-3.

**IAP20 Rec'd PCT/PTO 21 DEC 2005**

Respectfully submitted,

  
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Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 126363		APPLICATION NO. New U.S. National Stage of PCT/JP2004/007252 <b>10/201865</b>	
INFORMATION DISCLOSURE STATEMENT  (Use several sheets if necessary)				APPLICANTS Nobuaki MITAMURA et al.			
				FILING DATE December 21, 2005		GROUP	

U.S. PATENT DOCUMENTS						
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS

FOREIGN PATENT DOCUMENTS						
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS
	1	JP A 11-147786 w/ abst & transl	6/2/1999	JAPAN		
	2	JP A 2000-178099 w/ abst & transl	6/27/2000	JAPAN		
	3	JP A 2002-201093 w/ abst & transl	7/16/2002	JAPAN		

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)		
	4	VORONKOV, "The Mechanism of Swirl Defects Formation in Silicon," Journal of Crystal Growth, Vol. 59, pp. 625-643 {1982}
	5	DUPRET et al., "Global Modelling of Heat Transfer in Crystal Growth Furnaces," Int. J. Heat Mass Transfer, Vol. 33, No. 9, pp. 1849-1871 {1990}

EXAMINER	DATE CONSIDERED
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

Date: December 21, 2005